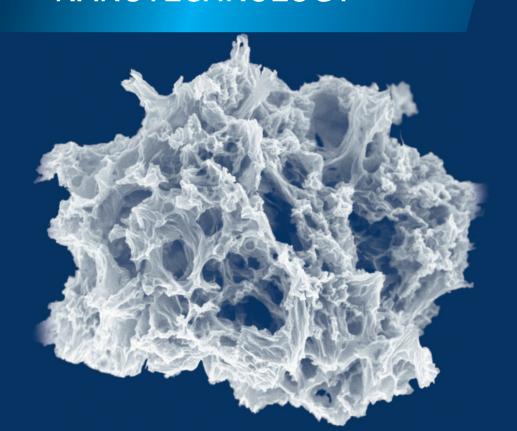




Ural Center for Shared Use

"MODERN

NANOTECHNOLOGY"



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#### Ural Center for Shared Use "MODERN NANOTECHNOLOGY" (UCSU MN)

Ural Center for Shared Use «Modern Nanotechnology» of the Ural Federal University:

- specializes in scientific research, services and experimental development
- has a unique complex of expensive analytical and technological equipment
- · has qualified staff
- uses certified measurement methods

#### What do UCSU MN clients receive?

- solving important production problems
- targeted staff development
- accelerated development of innovative solutions
- authoritative conclusions about product parameters

#### What do the clients of the UCSU MN save on?

- on the purchase of expensive equipment
- · on long and expensive operator training
- on maintenance of analytical equipment



Opening ceremony of the Center took place on December 12th, 2007.



UCSU was created in 2007-2008 on the basis of UCSU "Scanning Probe Microscopy" (opened in UrFU in 2002), equipment purchased under the Innovative Educational Program of UrFU.

In 2010, equipment supplies were carried out under 2008-2010 Federal Program of Nanoindustry Development in Russian Federation.

Address: Russia, Ekaterinburg, Kuybysheva str., 48

Director UCSU

Professor Shur Vladimir Yakovlevich, Doctor of Science

Phone: +7 (343) 389 95 68 e-mail: vladimir.shur@urfu.ru



#### Ural Center for Shared Use

# «MODERN NANOTECHNOLOGY» Ural Federal University (UCSU MN, UrFU)

#### The main goals for UCSU are the following:

- Enhancement of the technical facilities of UrFU by providing the unique up-to-date scientific and technological equipment;
- Development of the cooperation in the area of nanotechnology with the institutes of the Ural Branch of Russian Academy of Sciences, scientific organizations and major industrial and business companies of the Ural Region;
- Improvement of the education level in natural sciences departments of UrFU, including nanotechnology area;
- Integration of the creative capabilities of UrFU scientific groups.

#### The current objectives

- Support of fundamental and applied research in the field of physical and chemical material science related to nanomaterials and nanostructures;
- Support of development of advanced material and device technologies based on nanotechnology;
- · Creation and application of the new data banks and other IT products;
- Organization of the effective use of UCSU equipment to execute order of regional enterprises and companies, so as educational and scientific institutions;
- Exchange of experience, information, and educational programs with foreign partners;
- Providing the best conditions for scientific work of invited researchers from Russia and abroad.

#### PROBE NANOLABORATORIES NTEGRA, NT-MDT SI, Moscow, Zelenograd, Russia

NTEGRA platform is the basis for development of the scanning probe microscopy capabilities and their combination with other up-to-date research techniques.

NTEGRA family includes the equipment for scanning probe microscopy investigations in ambient and special conditions:in vacuum, at high and low temperatures, in liquids, etc.

#### Basic modes for NTEGRA family:

Contact and non-contact atomic-force microscopy
Scanning tunneling microscopy and spectroscopy
Two scanning regimes: by sample and by probe
Surface potential microscopy
Scanning capacitance microscopy
Electrostatic force microscopy
Magnetic force microscopy
Force modulation microscopy
Force and current lithography

Sample sizes: XY-resolution: Z-resolution: up to 100×100×15 mm<sup>3</sup> down to 10 nm down to 0,04 nm

### PROBE NANOLABORATORY NTEGRA-AURA,

NT-MDT SI, Moscow, Zelenograd, Russia



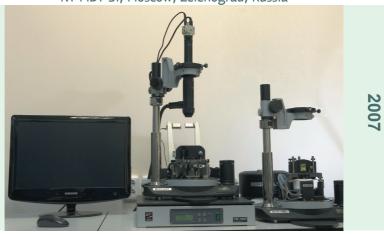
Measurements in vacuum and controlled atmosphere

Additional capabilities:

Measurements in gas media under controlled pressure Piezo-response force microscopy Contact scanning capacitance microscopy Atomic-force acoustic microscopy Measurements in liquid Voltage application: Sample heating:

up to 200 V up to 300 °C

#### PROBE NANOLABORATORY NTEGRA-THERMA, NT-MDT SI, Moscow, Zelenograd, Russia



Measurements in wide temperature range

Additional capabilities:

Measurements with precise drift compensation

in temperature range: from -30 °C to 200 °C

High-stable measurements with atomic resolution

in atomic-force microscopy mode

Measurements in lateral and longitudinal magnetic field

Sample heating: up to 300 °C

Measurements in liquid

### PROBE NANOLABORATORY NTEGRA-PRIMA,

NT-MDT SI, Moscow, Zelenograd, Russia

2007



Basic model - a multifunctional instrument to solve the routine problems related to scanning probe microscopy

Additional capabilities:

Voltage application:

Nanoindentation

Measurements by nanosclerometric module:

Young modulus:

hardness:

Usage in educational process

up to 50 V

from 1 to 1000 GPa from 1 to 150 GPa

### SCANNING PROBE MICROSCOPE MFP 3D SA, Asylum Research, USA



2013

Highest sensitivity, broad spectra of local electrical measurements

Sizes of samples:

XY resolution:

Z resolution:

Application of voltage:

Local properties, which can be measured: micro-u nano-relief of the surface:

range of heights:

Conductivity and spreading resistance:

registered current:

Work function of electrons

Spatial distribution of surface potential

Electromechanical properties

Spatial distribution of magnetic properties

up to 100x100x15 mm<sup>3</sup>

up to 10 nm up to 0.04 nm

up to 200 V

up to 0.04 nm

above 1 nA

2014

#### SCANNING NANO-HARDNESS TESTER NANOSCAN-4D, Technology Institute for Superhard and New Carbon Materials, Russia



Measuring of hardness and elastic module by nanoindentation and surface topography on nanometer scale

Test forces: 0.1—1000 mN Hardness: 0.001—80 GPa Young modulus: 0.01—1000 GPa Maximum specimen dimensions: 100x100x80 mm³

Measurement of length: X and Y axes:  $0.02-90 \mu m$  Z-axis:  $0.004-9 \mu m$ 

### PROBE NANOLABORATORY NTEGRA-Spectra, NT-MDT, Moscow, Zelenograd, Russia



Integration of scanning probe microscopy with confocal microscopy and Raman spectroscopy

Additional capabilities:

Spectroscopy and optical microscopy

effect of giant Raman scattering amplification

in-plane resolution:

up to 50 nm

Scanning laser confocal microscopy

including bulk scanning

Confocal fluorescence microscopy and spectroscopy

including bulk scanning

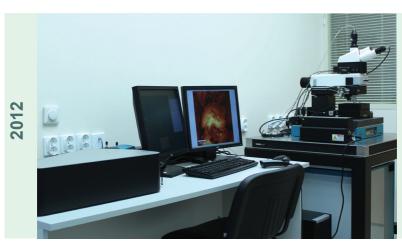
Scanning near-field optical microscopy

Imaging of the same sample area

with atomic-force and optical methods

Operations with transparent and nontransparent samples

#### CONFOCAL RAMAN MICROSCOPE Alpha 300 AR, WiTec, Germany



Nondestructive chemical analysis and surface relief mapping

Confocal microscopy in reflected light Fluorescent and Raman spectroscopy

Large area mapping:

3D layer mapping

Automated sample positioning: Excitation laser wavelengths:

Optical resolution (for laser 488 nm):

Vertical:

Lateral:

Spectral resolution:

**Detector:** 

up to 25x25 mm<sup>2</sup>

by X, Y and Z axes

about 500 nm about 400 nm 0.72 cm<sup>-1</sup> EMCCD camera

#### WORKSTATION AURIGA CrossBeam, Carl Zeiss, Germany



201

Study of morphology, chemical and structural material properties with nanoscale resolution

Scanning electron microscope with focused ion beam, electron backscatter diffraction (EBSD), energy-dispersive X-ray spectroscopy (EDS), local charge compensation, and E-beam lithography

Scanning Electron Microscopy:

Electron gun: Schottky field emitter
Resolution: 1.0nm @ 15kV, 1.9nm @ 1kV
Magnification: 12x—1000000x
Acceleration voltage: 0.1—30kV

Focused Ion Beam:

Ion gun: Ga liquid metal ion source
Resolution: <2.5nm @ 30kV
Magnification: 300x—500000x
Acceleration voltage: 1.0—30kV

### SCANNING FIELD EMISSION ELECTRON MICROSCOPE MERLIN, Carl Zeiss, Germany

2016



Scanning electron microscope for a wide range of studies

- · Observation in secondary electrons
- Observation in reflected electrons with selection by work function and electron escape angle
- Charge compensator with the possibility of *in situ* cleaning of the sample surface
- 4 manipulators for measuring the conductivity of samples in the microscope chamber
- EBIC detector for the study of the electrical properties of semiconductor materials
- Energy dispersive microanalysis

Beam current:

Accelerating voltage:

Thermal stage for studying the dynamics of phase transitions:

up to 300 nA from 20 to 30 kV

from -180 to +400°C

#### SCANNING ELECTRON MICROSCOPE EVO LS 10, Carl Zeiss, Germany



Scanning electron microscope for wide range of life science samples

Electron gun: Resolution:

Accelerating voltage:

Pressure Range: Detectors

3 nm @ 30 kV, 20 nm @ 1kV 0.1—30 kV 10—3000 Pa

thermionic emission (W, LaB6)

Everhart-Thornley Secondary Electron Detector Variable Pressure Secondary Electron Detector Extended Pressure Secondary Electron Detector Backscattered Electron Detector (4QBSD) Energy Dispersive Spectrometer (EDS)

Scanning transmission electron microscopy detector

Environmental Electron Microscopy

Peltier cooling stage

Sample preparation system (Quorum Tech, UK)

Ultramicrotome: section thickness 5 nm — 15 µm

Rotary-pumped combined sputter coater and SEM carbon coater Q150RES

Critical Point Dryer K850

CryoSEM preparation system PP3010T

#### SCANNING ELECTRON MICROSCOPE VEGA 3 SBH, Tescan, Czech Republic

020



Scanning electron microscope with an energy-dispersive attachment for elemental microanalysis and vacuuming of samples

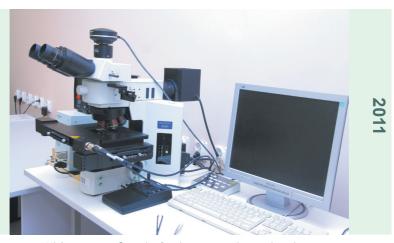
Resolution:

Magnification: Electron gun:

Vacuum operating value in the chamber:

3 nm at 30 kV 8 nm at 3 kV 4.5 to 1,000,000 tungsten heated cathode with thermionic emission less than  $9 \times 10^{-3}$  Pa

#### UNIVERSAL RESEARCH MICROSCOPE BX61 Olympus, Japan



Wide range of optical microscopy investigations with automatic image analysis

#### Specifications:

Maximum magnification:

1000x

Reflected light Transmitted light Polarized light Dark field

Phase contrast

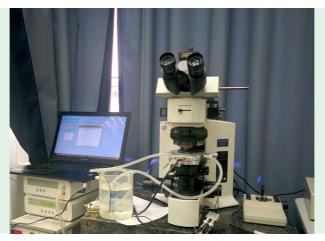
Fully motorized

Software for image registration and image analysis

1000x

#### UNIVERSAL RESEARCH MICROSCOPE BX51 Olympus, Japan

007



Wide range of optical microscopy investigations with automatic image analysis

#### Specifications:

Maximum magnification:

Reflected light Transmitted light

Polarized light

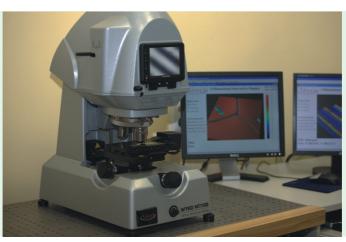
Dark field

Phase contrast

Fully motorized

Software for image registration and image analysis

### OPTICAL PROFILER Wyko NT1100, Veeco Instruments, USA



3D surface metrology: noncontact fast measurements of surface topography from nanometer scale roughness through millimeter scale steps

Measurement techniques:

vertical scanning interferometry

Z-range:

phase-shifting interferometry

Z-range:

Magnifications:

Lateral spatial sampling:

Field of view:

Auto stitching:

3 nm — 1 mm

0.1 nm — 160 nm

2.5x-100x

80 nm — 8 µm

 $50 \mu m - 5 mm$ 

up to 100 mm

### NON-CONTACT OPTICAL VIDEO MEASURING MICROSCOPE Kestrel-200/Peregrine, Vision Engineering, UK

010



Wide range of fast and accurate non-contact 2-axis measurements

Dynascope™ Optical head and Video processor QC300 with automatic edge detection.

Pattern Approval Certificate of Measuring Instruments "Non-contact measurements system".

#### Specifications:

magnification: x10, x20, x50

reflected and transmitted light

measurement table: 150x100 mm<sup>2</sup> measurement accuracy: 7 µm

### THERMAL STAGES FOR OPTICAL MICROSCOPY TS1500EV-7/6 and THMS600, Linkam Scientific, UK



Investigations by optical and confocal Raman microscopies in a wide temperature range with controlled atmosphere and humidity

Temperature range: Heating/cooling rate: Temperature stability:

Humidity control range: Humidity stability: Vacuum: -196°C to 1500°C 0.1 to 200°C/min 0.1°C for the range -196°C to 600°C 1°C for the range 600°C to 1500°C 5% to 90% ±0.5% up to 10<sup>-3</sup> mbar

2007

### THERMOGRAVIMETRIC ANALYZERS STA 409 PC Luxx, Netzsch, Germany

Simultaneous Thermo Analysis (TG-DSC or TG-DTA) in wide temperature range

Sensitivity: 0.001 mg
Mass variation measurement ranges: ±20 mg, ±200 mg, ±2000 mg
Accuracy: 1 % of measurement range
Peak load: 18 g

Temperature range: 25—1500 °C Rate of temperature change: 0.1—50 °C/min

Atmosphere: neutral, oxidative, reducing

### SYNCHRONOUS DSC/DTA INSTRUMENT, THERMOGRAVIMETRIC ANALYZER PYRIS 1 TGA, Perkin-Elmer, USA



200

Representative of a new generation of thermal analyzers, combining high sensitivity, accuracy and reproducibility

Temperature range Balance sensitivity Weighing accuracy  $50...1500~^{\circ}\text{C}$   $0.1~\mu\text{g}$  not less than 0.02%

### DILATOMETER DIL 402C, Netzsch, Germany



Measurement of linear thermal dilatation of solid and liquid powders, pastes and ceramic fibers

c-DTA software for calculation of endo-/exothermic effects simultaneously with measurement of sizes change

Connection with mass-spectrometer is available

Horizontal sample holder

Measurement ranges: 0.5/5 mm

Resolution: 0.125 nm per order, 1.25 nm per order

Contact pressure with sensor: 0.15—0.45 N

Adjustable range of sample length: 25 mm

Temperature range: from RT to 1600 °C

### SPECIFIC SURFACE AREA ANALYZER TriStar 3000, Micromeritics, USA



2008

High-quality surface area and porosimetry measurements on solid materials by using the technique of gas adsorption and desorption

Measured parameters:

pores radius

pores volume distribution

specific surface area

Minimal surface area: Minimal pore volume: Simultaneous analysis:  $0.01 \text{ m}^2/\text{g}$  $4x10^{-6} \text{ cm}^3/\text{g}$ up to 3 samples

### HYBRID QUADRUPOLE HIGH RESOLUTION MASS SPECTROMETER XEVO QToF with ACQUITY UPLC system, Waters, USA



Quadrupole (Q) and time-of-flight (Tof) high resolution mass spectrometer

The basic components of the system are: Waters ACQUITY UPLC system Waters Xevo QTof mass spectrometer

Allows identifying, quantifying and confirming the broadest range of compounds in the most complex and challenging samples lonization source:

Xevo electrospray (ESI)

Location: room 158a

# GAS-ANALYSIS SYSTEM BASED ON QUADRUPOLE MASS SPECTROMETER STA 409 Luxx/QMS 403 C, Aëolos, Netzsch, Germany



Qualitative and quantitative analysis of gaseous decomposition products of inorganic matters

Connection to the simultaneous thermal analyzer

Mass range: 1-300 a.m.u. Resolution: > 0.5 a.m.u. Registration threshold:  $> 2x10^{-14}$  mbar

 $\begin{array}{ccc} & > 1 \text{ ppm} \\ \text{Connection type:} & \text{capillary} \\ \text{Capillary maximal temperature:} & 300 \, ^{\circ}\text{C} \end{array}$ 

Ion source: electron impact, energy 70 eV
Sensor: Faraday and SEV
Vacuum system: turbomolecular and diaphragm pumps

# COUPLED PLASMA iCAP 6500 Duo, Thermo Scientific, USA and LASER ABLATION SYSTEM NWR 266, ESI, USA

ATOMIC-EMISSION SPECTROMETER WITH INDUCTIVELY

2007, 2014



Quantitative and qualitative elemental analysis with simultaneous detection of up to 40 elements

Spectral range: from 166 to 867 nm

Spectral bandpass at 200 nm wavelength: 7 pm

A new-generation semiconductor solid state detector: CID86

Wide range of concentrations measured

Possible analysis of:

high saline solutions

hydrofluoric acid containing samples organic solvents containing samples

Analysis of natural and waste water for heavy metals

for environmental monitoring:

ferrous and non-ferrous materials environmental objects (water, soil)

Laser wavelength: 266 nm

### ATOMIC ABSORPTION SPECTROMETER SOLAAR M6, Thermo Scientific, USA



Qualitative elemental analysis of different samples for inorganic components

Flame and furnace analysis Definition limits for Al detection:

flame analysis:

furnace analysis:

Amount of possible elements determination:

Spectral range:

Spectral bandpass at 200 nm:

28 μg/l 0.052 μg/l

from 180 to 900 nm

0.5 nm/mm

40

2008

#### LIQUID CHROMATOGRAPH LC-20, Shimadzu, Japan



Compounds separation from liquid complicated mixtures based on different passing speed through the chromatographic column under the high pressure

Operational ranges:

pH: 1—13

temperature: 4—35 °C

flow-rate setting: 0.0001 to 10 ml/min

flow-rate precision: 0.3 %

Spectrophotometric UV-Vis detector:

with temperature-controlled flow cell

noise level: 0.5×10<sup>-6</sup> AU

Possibility of the organic toxicants determination:

in natural objects in waste waters

# GAS CHROMATOGRAPH WITH GAS-CARRIER DIGITAL CONTROLLER, Thermo Focus GC., Thermo Scientific, USA



200

Separation of complex mixtures based on difference in volatility, solubility, or adsorbability

Identification and quantitative determination of components

Environmental analysis for organic contaminants

The state of the s	
up to 400	
from RT to 350°C	
0.1—120 °C/min	
7	
270 s	
270 s	
300 Hz	

### LASER ANALYZER OF ELEMENTAL COMPOSITION LEA–S500, SOL instruments, Belarus



2021

Qualitative and quantitative determination of the elemental composition of materials and substances in solid and powder forms by laser-spark emission spectrometry

Definable elements: from hydrogen (H) to uranium (U)

Concentration measurement range: 0.01ppm to 100%

Spectral range: 175-800 nm Spectral resolution: 0.014 nm

Spectral resolution: 0.014 nm Sample size: from 12×12×2 mm<sup>3</sup> to 75×75×40 mm<sup>3</sup>

Emission spectra excitation system:

Solid state two-pulse

Q-switched laser

on YAG:Nd3+ (1064 nm)

Laser spot diameter on the sample surface: 0.05–0.2 mm

# FOURIER TRANSFORM INFRARED SPECTROMETER WITH EXPANDED SPECTRAL RANGE Nicolet 6700, Thermo Scientific, USA



Measurement of IR absorption spectra and diffuse reflection for identification of inorganic and organic materials, polymers and coordination compounds

Spectral range: 27000—50 cm<sup>-1</sup>
Spectral resolution: 0.4 cm<sup>-1</sup>
Wave number error amount: 0.01 cm<sup>-1</sup>
Accessories:

for attenuated total reflection (ATR) for diffuse reflection full-sized additional experimental module AEM dry-air generator

Identification in automatic mode using the spectra data library Analysis of fluid, viscous, and solid samples without special preparation.

### SPECTROFLUOROMETER Fluorat-02-Panorama, Lumex, Russia



Determination of time-resolved fluorescence, and time dependence in the processes of chromatographic separation

Spectral range:

Spectral bandwidth of monochromators:

Wave length measurement accuracy:

Duration of single measurement:

Measurements possible:

at ambient temperature

at temperature of liquid nitrogen

from 220 to 840 nm

< 10 nm

< 3 nm

< 10 s

#### UV-VIS-NIR DOUBLE BEAM SPECTROPHOTOMETER, Cary 5000, Agilent Technologies, USA



Measurements of absorbance and reflectance at specific wavelengths or over a range for absolute or relative comparisons of solid and liquid samples

Wavelength range: 175—3300 nm Limiting resolution: UV-Vis < 0.048 nm NIR < 0.2

Spectral bandwidth:

UV-Vis 0.01 to 5.00 nm, 0.01 nm steps, motor driven

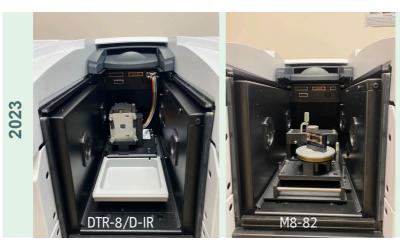
NIR 0.04 to 20, 0.1 nm steps, motor driven Wavelength accuracy: UV-Vis  $\pm$  0.08 nm

0.08 nmNIR ± 0.4

Wavelength reproducibility: UV-Vis < 0.02 nm

NIR < 0.08

### PHOTOELECTRIC ATTACHEMENTS DTR-8/D-IR & M8-82, SOL Instruments, Belarus



DTR-8/D-IR attachment with integrating sphere for measurement of transmittance and diffuse reflection coefficient with the possibility of excluding the normal component.

M8-82 attachment for measuring of absolute specular reflection coefficient at a variable angle.

Study of the optical characteristics of structures with microrelief, colloidal solutions of micro and nanoparticles of any concentration, powders, ceramics.

Combined and separate measurement of diffuse and specular reflection

Spectral range: Integrating sphere diameter: Angle of incidence range: Angle setting step: 220—1100 nm 50,8 mm 8—82°

0,5°

## TOTAL REFLECTION X-RAY FLUORESCENCE (TXRF) SPECTROMETER

Nanohunter, Rigaku Corporation, Japan



Investigations in the field of material science, microelectronics, products composition control, legal expertise

#### Main features:

2010

Power of Mo and Cu X-ray tubes: 0.05 kW Elemental range: from Al to U Sensitivity:  $10^{-7}$  wt.% Glancing angle range:  $0-2^{\circ}$  Angular scanning resolution: 0.01° Radiation penetration depth: up to 500 nm

Measurements in air

Maximum sample size: 100x100x5 mm

### MULTIFUNCTIONAL X-RAY PHOTOELECTRONIC SPECTROMETER K-Alpha, Thermo Fisher Scientific, UK



201

Non-destructive analysis of the elemental composition, empirical formula, chemical and electronic state of atoms present in the material

lon cannon with charge neutralization function 128-channel analyzer for building high quality spectral maps

Range of measured kinetic energies:

Analyzer transmission energy: X-ray spot size:

Maximum power:

5–1500 eV 1-400 eV 30-300 μm (step 5 μm)

not less than 72 W

2008

#### SQUID-MAGNETOMETER MPMS XL7, Quantum Design, USA



Measurement of magnetic properties with high sensitivity in wide temperature range

Magnetic field range:	±7.0 T
Intrinsic field uniformity over 4 cm:	0.01 %
Field stability:	10 <sup>-6</sup> /hour
Temperature range:	1.9—800 K
Differential sensitivity:	10 <sup>-8</sup> emu
Range of measurements:	± 300 emu
Sensitivity at AC susceptibility measurement:	10 <sup>-8</sup> emu

#### VIBRATING SAMPLE MAGNETOMETER 7407 VSM, Lake Shore Cryotronics, USA



2013

Measurements of magnetic moments of bulk and thin film samples

Sensitivity:
Range of magnetic moments:
Temperature range:
Magnetic field:
Optional sample rotation system
Equipped with sample evacuation system
and Helmholtz coils
Equipped with option for measurements
of electrical resistivity
Electromagnet poles diameter:

10<sup>-7</sup> emu 10<sup>-7</sup>—1000 emu 4.2—1300 K up to 23 k0e

51 mm

2012

#### COMPUTER CONTROLLED HYSTERESISGRAPH Permagraph L, Magnet Physik, Germany

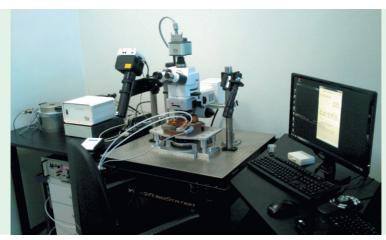


Measurement of magnetic hysteresis characteristics of magnetic materials

Magnetic field intensity:
Sample heating:
A set of compensated measuring coils
of 10, 15, 26 and 40 mm diameters
A set of certified standard nickel samples
Hard ferrite magnet reference sample

up to 32 k0e up to 200 °C

### MAGNETO-OPTICAL KERR-MICROSCOPE Evico magnetics, Germany



2015

Visualization of magnetic domains and automatic measurement of magnetooptical hysteresis loops

Polar, longitudinal and transverse Kerr effects can be used

Based on the Carl Zeiss polarizing microscope

Linear dimensions of the observation area: 0.1—5 mm

Optional overview polarizing microscope

Linear dimensions of the observation area: 8—30 mm

Light source - 8 highly stable LEDs

Wavelength: 450 nm

Digital camera with resolution:  $1344 \times 1024$  pixels

Horizontal magnetic field: 0.1—1300 mT Vertical magnetic field: up to 900 mT

Substrates' diameter: up to 76 mm

### AUTOMATED MEASURING SYSTEM FOR MAGNETIC PARAMETERS TESTING MagEq MMS, AMT&C LLC, Russia

2015



Direct measurements of adiabatic temperature changes initiated by changes of magnetic field and heat capacity at different magnetic fields

Operating temperature range: 110—360 K
Magnetic field range: 0.018—1.755 T
Speed of magnetic field change: 0.25—4.7 T/s
Measurements uncertainty:

adiabatic temperature changes: 0.1 K heat capacity: 3 %

Automated and manual operating modes

### PHYSICAL PROPERTIES MEASUREMENT SYSTEM PPMS Dyna Cool, Quantum Design Inc., USA



201

System for precise measurements of the characteristics of various materials in a magnetic field (heat capacity, electrical conductivity, magnetic susceptibility in an alternating field)

Cryogenic-free integrated helium liquefaction system Continuous operation at temperatures below 4.2 K Vacuum pump

Interval of working magnetic fields: Operating temperature range:

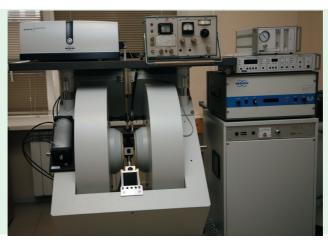
Temperature sweep rate:

Field resolution value:

Field stability:

from -9 to +9 T 1.9—400 K 0.01—6 K/min 0.02 mT at < 1 T 0.2 mT at < 9 T 1 ppm/hour

#### ELECTRON SPIN RESONANCE SPECTROMETER EMX Plus, Bruker, Germany



Continuous wave detection Electron Spin Resonance (EPR) and Electron-Nuclear-Double Resonance (ENDOR) at frequencies up to 100 MHz

Magnet system:

14.5 kG maximal magnetic field strength: 72 mm

air gap:

High sensitivity probe head:

optical window

quality factor: more than 15 000 1.6 x 109 spins/G absolute sensitivity:

sample access: 10 mm

**ENDOR** system:

frequency: up to 100 MHz

Temperature control systems:

helium system: 3.8-300 K 100-500 K nitrogen system:

#### X-RAY POWDER DIFFRACTOMETER XRD-7000S, Shimadzu, Japan



X-ray diffraction analysis of polycrystalline materials

Cu-KA-radiation, long fine focus (LFF): Vertical  $\theta$  -2 $\theta$  goniometer radius:

Minimum step size:

Angle reproducibility:

In-plane rotation of the sample (1-60 rpm) in combination with oscillation around the goniometer sample axis  $(\theta)$ 

Scanning range: Auto 5 position sample changer (ASC 1001)

High-temperature attachment HTK 1200N (Anton Paar) XRD diffraction in air and non-aggressive gas mixtures at temperature range:

0.4×12 mm 200—275 mm  $0.0001^{\circ} (\theta)$  $0.0002^{\circ}$  (20)

+/-0.0002°  $-12 - +164^{\circ} (2\theta)$ 

25-1200 °C

#### X-RAY DIFFRACTOMETER EQUINOX 3000, Inel, France



Investigation of the kinetics of structural phase transitions in solid state, X-ray phase and structural analysis

Curved position-sensitive detector

Angular interval 2θ:

Monochromatic radiation:

Holder:

Vacuum X-ray studies at temperatures:

Thin films investigation:

Real time capture of diffraction patterns from crystal samples

Location: room 320

90°

CuKA1

30 samples

up to 1200 °C

### EQUIPMENT COMPLEX FOR MEASUREMENTS OF MATERIALS PROPERTIES

#### TEST MACHINE AG-50kNXD, Shimadzu, Japan



2008

Carrying out mechanical tests for stretching and compression of various materials

Automatic-mode construction of deformation curves in standard coordinates and determination of the following mechanical characteristics of materials in the state of stretching or compression:

proportionality limit fluidity limit strength limit strengthening coefficient

sample lengthening before disintegration

Load range: 1 N — 50 kN

Accuracy corresponds to the first class

### PHYSICAL PROPERTIES MEASUREMENT SYSTEM DMS-1000, Dryogenic, UK

2008



Cryogen-free investigation of various physical properties in wide temperature range and high magnetic fields

Properties investigated:

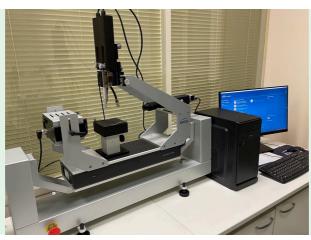
specific heat electrical resistivity Hall effect

magnetic susceptibility

Temperature range: Magnetic fields:

0.1—300 K up to 12 T

### CONTACT ANGLE MEASURING DEVICE DSA25S, KRUSS, Germany



2022

Contact angle measurement by sessile drop method

Measuring range: 1...180° Resolution:  $\pm 0.1$ ° Dosing step: 0.1  $\mu$ l Dosing rate: 10 ... 1400  $\mu$ l/min Surface temperature control

Surface temperature control

and wetting liquid -10 ... 450°C

Software-based calculation of the contact angle from the shape of a drop Software-based calculation of the surface free energy from the contact angles

#### TENSIOMETER K100C, KRUSS, Germany

022



Tensiometer with a module for measuring the critical concentration of micelle formation.

#### Available measurement types:

surface and interfacial tension methods Du Nui rings and Wilhelmy plates critical micelle concentration (CMC) wettability of powders, films and fibers

Measurement range:

1 ... 2000 mN/m

The CMC measurement module allows:

determination and building a graph of the CMC points determination of the point of synergy of surfactant mixtures calculation of the surface of one molecule calculation of Gibbs free energy of absorption

#### MULTIFUNCTIONAL SYSTEM FOR COMPREHENSIVE EVALUATION OF PIEZO - AND FERROELECTRIC MATERIALS aixPES, aixACCT, Germany



2012

Measurement and analysis of ferroelectric, piezoelectric, pyroelectric and dielectric properties in thin films and bulk materials

Investigation technique:

Dynamic and static hysteresis loops of

polarization

strain

dielectric constant

piezoelectric coefficient

Pyroelectric measurement

Switching and leakage current measurement

Investigation of fatigue and aging process

Precision low current preamplifier

Sample holders for thin films and bulk samples

operating temperature range: 20 — 200 °C

Internal and external voltage amplifier, max voltage up to: 10 kV

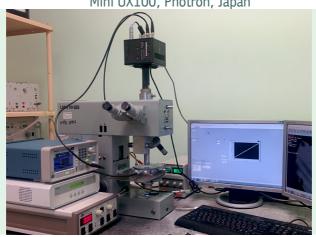
Precision displacement sensor

(laser interferometer) resolution: 0.3 nm

Hysteresis loops measurement frequency: 10mHz — 10MHz

OPTICAL MICROSCOPE LMA10, Carl Zeiss, Germany WITH HIGH SPEED VIDEO SYSTEM Mini UX100, Photron, Japan

2013

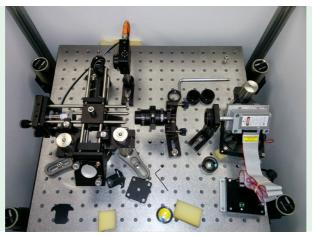


Conducting studies of ferroelectric materials using a combination of optical microscopy and electrical techniques in a wide temperature range

Simultaneous recording of the switching current and visualization of the domain structure Arbitrary-shaped electric field pulses Modified Merz scheme

Maximum electrical voltage: Temperature range: Video shooting speed: 10 kV -40 - 600 °C 5000 fps at 1280×1000 px 20,000 fps at 1280×248 pixels 100,000 fps at 1280×32 pixels

### INTERFEROMETRIC MEASUREMENT SETUP Thorlabs, USA



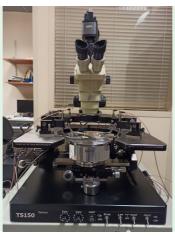
707

Measurement of electromechanical deformations with high accuracy in wide temperature range

Michelson-Morley interferometer scheme Selective amplification of the signal at the reference frequency PID feedback

Minimum detectable displacements: Measurement frequency: Temperature range: down to 10<sup>-4</sup> Å 10 Hz — 40 kHz 0 — 200°C

### PROBE STATION TS150, MPI Corporation, Taiwan



202

Testing of semiconductor, optoelectronic, micro- and nano-electromechanical systems with precision probe positioning and process control with an optical microscope

Sample holder size:	150 mm
Number of probe manipulators:	4 pcs
Three-axis positioning accuracy:	1 μm
Vertical adjustment:	40 mm
Displacement repeatability:	1 um

### CLEAN ROOM ENVIRONMENT class 100, CG "ROST, Russia



Clean room for operations that require a minimum amount of pollution in the ambient air, including photolithographic processes

Room type: turbulently ventilated clean room Purity class: class 100 Air exchange rate: 300 volumes per hour Temperature maintenance accuracy: 1°C

### LABORATORY SPIN COATER SM180-HP250HDMS, Sawatec Solutions, Liechtenstein



Resist spin coating and thermal backing

Independent coater and hotplate/coolplate in one system
Spin coating of wafers with uniform resist films
After-development drying and high-temperature
processing of resist films
Soft and hard backing of resist films

(including vacuum or  $N_2$  atmosphere)

Wafer annealing and HMDS primer deposition Separate resist deposition and thermal processing

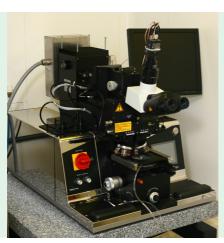
Wafers: Si, GaAs, LiNbO<sub>3</sub> and others

Maximum wafer size: 51, GaAS, LINDO<sub>3</sub> and Others
150 mm (6")

Maximum bit size: 100 mm

The equipment is installed in the clean room (class 100) intended for contact photolithography

#### MANUAL CONTACT MASK ALIGNER SUSS MJB4, Suss MicroTec, Germany



Alignment of photomask with wafer and resist exposition for contact lithography

Contact lithography modes:

soft contact hard contact

rough vacuum contact

vacuum contact

gap printing:

Spatial resolution: Wafers:

Wafer size:

Bit size:

 $0-50 \, \mu m$ up to 0.6 µm

Si, GaAs, LiNbO<sub>3</sub> and others 100 mm (4") from 10 x 10 mm<sup>2</sup>

The equipment is installed in the clean room (class 100) intended for contact photolithography

### WET PROCESS SYSTEM OPTIwet ST30, SSE, Germany



200

Automatic multi-step spin wafer cleaning, resist development, and resist stripping

Solvent cleaning

RCA SC1 (NH<sub>4</sub>O $\ddot{\rm H}$ : H<sub>2</sub>O<sub>2</sub>) and Piranha (H<sub>2</sub>SO<sub>4</sub>:H<sub>2</sub>O<sub>2</sub>)

cleaning with heating:

Deionized ultrapure water rinsing with heating:

Spin drying with gaseous nitrogen

Max. spin speed:

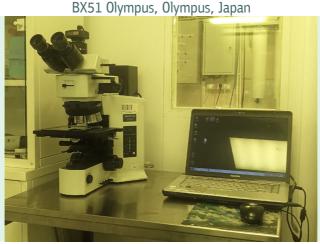
up to 80 °C

up to 80 °C

up to 4000 rpm

The equipment is installed in the clean room (class 100) intended for contact photolithography

## OPTICAL PHOTOLITHOGRAPHY QUALITY CONTROL SYSTEM



Optical microscopy in cleanroom environment for testing the objects sensitive to contaminations

Imaging modes:

Reflection Transmission Bright/Dark field Polarized light

Illumination: 100 W Objectives: 1.25x, 5x, 10x, 20x, 50x, 100x

Digital camera with imaging software

The equipment is installed in the clean room (class 100) intended for contact photolithography

### WATER PURIFICATION SYSTEM Elix 10, Millipore, France



Production of ultrapure (type I) deionized water with recirculation line

Resistivity (25°C): TOC concentration: Removal of Si: Peak productivity: Average productivity: Recirculation line pressure: above 18 M0hm⋅cm below 30 µg/l above 99.9 % above 12 l/min above 200 l per 24 hours about 2 bar

### COMBINED VACUUM THIN FILMS DEPOSITION SYSTEM Auto 500 Edwards, BOC Edwards, UK

008



Deposition of metal and dielectric thin films by electron-beam evaporation and DC/RF magnetron sputtering

Wafer diameter: up to 100 mm

Materials:

elements: Al, Cu, W, Au, Pt, Cr, Nb, Ta, Ni, Mo, C compounds: TiN, NiCr, Si<sub>3</sub>N<sub>4</sub>

oxides:  $TiO_{2}$ ,  $Ta_{2}O_{5}$ ,  $Al_{2}O_{3}$ ,  $SiO_{2}$ ,  $In_{2}O_{3} - SnO_{2}^{0}$ 

Deposition of wide range of conductor, semiconductor,

and dielectric materials applicable

for magnetron sputtering

Plasma glow discharge wafer cleaning

Wafer heating: up to 300 ℃

### MAGNETRON SPUTTERING SYSTEM ATC ORION 8 UHV, AJA International, USA



800

Sputtering of multilayer and composite metal, dielectric and magnetic films

Five independent magnetron sputtering sources

(2 DC and 3 RF power)

Turbomolecular pumping system

vacuum: Rotating substrate holder

heating:

Substrate holder cooled by liquid nitrogen Three independent gas feed lines

Computer control system

not less than 5\*10<sup>-7</sup> Torr

up to 800 °C

### REACTIVE ION ETCHING SYSTEM Plasmalab 80 Plus RIE, Oxford Instruments, UK



Plasma reactive ion etching of metals, Si and Si compounds, and dielectrics

Metals:

Si compounds: Wafer diameter:

Roughing pump productivity:

Turbo molecular pump with inert gas purge:

5 reactive gas lines with independent automatic mass flow control

reactive gas:

W, Nb, Ta, Mo SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub> up to 200 mm 95 m<sup>3</sup>/h

0<sub>2</sub>, Ar, CF<sub>4</sub>, CHF<sub>3</sub>, SF<sub>6</sub>

### VACUUM COATING SYSTEM ELATO, IZOVAC, Belarus



Coating by electron-beam evaporation with preliminary ion-beam cleaning

Ultimate residual pressure:	$< 2 \times 10^{-4}  \text{Pa}$
Time to reach ultimate residual pressure:	< 12 hours
Time to reach a pressure of $8 \times 10^{-4}$ Pa in a clean chamber	
since shutter opening:	< 40 minutes
Heating temperature:	up to 350 °C
Temperature maintenance accuracy:	±5 °C
Electron-beam evaporation power:	6 kW
Substrate material:	LiNbO <sub>3</sub> , LiTaO <sub>3</sub>
Substrate diameter	76, 100 mm
Substrate holder rotation speed:	5—40 rpm
Substrate heating:	300 ± 5 °C
Substrate heating/cooling rate:	up to 5°C/min

### Q-SWITCHED SOLID-STATE ND:YAG LASER WITH HARMONIC GENERATORS Brilliant, Ouantel, France



Generation of high energy laser pulses in IR, visible, and UV spectral ranges (first, second, third, and fourth harmonics of 1064 nm)

Wavelengths: 1064, 532, 355, 266 nm

Pulse energy:

2007

 1064 nm:
 350 mJ

 532 nm:
 160 mJ

 355 nm:
 60 mJ

 266 nm:
 30 mJ

 Pulse duration:
 5—6 ns

Repetition rate: 10 Hz
Divergence: less than 0.5 mrad

Beam diameter: 4—6 mm

Laser head sizes: 150×500×80 mm<sup>3</sup>

### LASER SYSTEM FOR MATERIAL PROCESSING VL-300/40, Universal Laser Systems, USA



Laser marking, engraving, and cutting of wide range of materials

Pulsed CO, gas laser

Wavelength: Average radiation power:

10.6 μm 40 W

Scanning system:

Max. speed:

1.8 m/s

Max. operating area:

305×610 mm<sup>2</sup>

Positional accuracy:

±25 µm

Additional lens set for 10.6 µm wavelength

### EQUIPMENT SET FOR CHARACTERIZATION OF LASER BEAMS LaserStar, BeamStar FX50, Ophir, Israel



Measurement of various parameters of laser irradiation

Measurement of power and energy of cw and pulsed laser irradiation

Measurement of beam profiling

Determination of laser beam radius, divergence, and M² beam quality factor

Temporal pulse shape measurements

Power measurement range:

Spectral range:

Maximal beam size to measure:

Beam radius measurement accuracy:

30 nW — 10 W 350—1320 nm up to 4x6 mm<sup>2</sup> over ±1 %

#### ULTRASHORT LASER PULSES SETUP Avesta-Project Ltd., Russia



202

Ultrashort pulse laser setup for material processing, two-photon polymerization and lithography

Femtosecond laser TETA-10:

Wavelength: 1030 nm Pulse energy: up to  $400 \mu J$  Pulse width: 270 fs to 10 ps Pulse repetition rate: up to  $200 \ kHz$  Average power: 10 W

Parametric generator PARUS-NE-515:

Signal wave tuning range: 630 to 1020 nm Idle wave tuning range: 1040 to 2800 nm

External generator of the second and third harmonics AtsG-A-1030:

Wavelengths: 515 nm and 343 nm

### ULTRASHORT LASER PULSES SETUP Avesta-Project Ltd., Russia



Femtosecond pulse laser setup for processing of various materials with focused laser radiation

Wavelength: 1030 nm

Pulse energy:  $> 20 \mu J$  at frequency of 1 MHz

Pulse width: 270 fs

Pulse repetition rate: from 200 kHz to 1 MHz

Average power: 20 W

### PRECISION LASER MARKING SYSTEM MiniMarker 2 - M20, Laser Center LLC, Russia

2017



Precision marker based on a fiber laser with increased speed and quality characteristics

Laser wavelength Pulse duration Pulse repetition rate: Marked materials: 1064 nm 110 ns 20-100 kHz metals and alloys, painted and coated metal surfaces, ceramics, rubber, plastic, semiconductors, "tesa laser" foil, etc.

Positioning accuracy Software and hardware resolution Repeat positioning accuracy Beam travel speed

5 μm adjustable, up to 8.7 m/s

Location: room 101

 $\pm 150 \mu m$ 

2.5 µm

# EQUIPMENT COMPLEX FOR SYNTHESIS OF COLLOID SOLUTIONS OF METAL NANOPARTICLES

### LASER SYSTEM FOR MATERIAL PROCESSING Fmark-20 RL, Laser Technology Center, St.-Petersburg, Russia



2008

High speed and accuracy laser marking, engraving and cutting of wide range of materials

Pulsed ytterbium fiber laser

Wavelength:	1.05—1.07 μm
Frequency:	20—100 kHz
Max. power:	20 W
Max. pulse energy:	1 mJ
Service life:	30000 hours

Double-axis galvanometric scanning system:

operating area:	50x50 mm <sup>2</sup>
max. speed:	4.5 m/s
positional accuracy:	±2.4 μm

### PARTICLE SIZE, ZETA-POTENTIAL AND MOLECULAR WEIGHT ANALYZER Zetasizer Nano ZS, Malvern Instruments, UK



Measurement of size distribution, Zeta-potential and molecular weight of nano-and submicro-particles and molecules in colloid solutions

Parameters measured: hydrodynamic size, zeta potential and molecular weight

Temperature control range: Min. sample volume:

Size range

Molecular weight range

Zeta potential:

suitable size range: max. sample conductivity: min. sample volume: 0°C — 90°C +/- 0.1°C 12 μL

 $0.6 \text{ nm} - 8.9 \mu\text{m}$  $342-2x10^7 \text{ Da}$ 

3.8~nm —  $100~\mu\text{m}$  200~mS/cm  $150~\mu\text{L}$ 

## EQUIPMENT COMPLEX FOR SYNTHESIS OF COLLOID SOLUTIONS OF METAL NANOPARTICLES

### LASER DIFFRACTION PARTICLE SIZE ANALYZER SALD-7101, Shimadzu, Japan



7007

Measurement of particle size distribution in suspension by laser diffraction method

Measuring size range:

Light source: Light detector:

Inner volume of dispersing bath:

Disperser:

frequency:

output power:

Bath cell:

inner volume:

material:

15 nm — 250 µm UV semiconductor laser 81 elements in total 280 cm<sup>3</sup>

> 42 kHz 40 W

> 12 cm<sup>3</sup>

quartz glass

#### INFRARED CAMERA Avio H2640, NEC, Japan

013



### Carrying out thermographic measurements over a wide temperature range

Temperature measurement range: Imager accuracy: Spectral range of the thermal imager Detector type: Thermal imager detector size: Emissivity correction from -40°C to +2000°C  $\pm$  2°C,  $\pm$  2% of reading 8 ... 13  $\mu$ m uncooled microbolometer, VO<sub>2</sub> 640×480 pixels 1.00 ... 0.10 (step 0.01)

## PRECISION LAPPING AND POLISHING MACHINE PM5, Logitech, UK



2007

Precision lapping and polishing of crystalline wafers

Microprocessor control
Precision jig for wafer flatness and alignment control
Different lapping and polishing pads (cast iron, polyurethane)
Precision thickness measurement gauge
Optical autocollimator for precision
parallel specimen production

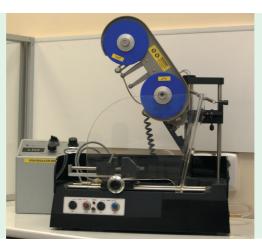
 $\begin{array}{lll} \text{Wafer diameter:} & \text{up to 83 mm} \\ \text{Disk diameter:} & 300 \text{ mm} \\ \text{Al}_2 \text{O}_3 \text{ abrasives:} & 3 \text{ } \mu \text{m} \text{ and } 9 \text{ } \mu \text{m} \\ \end{array}$ 

SiO<sub>2</sub> suspension for mechano-chemical

fine polishing for sub-nm surface roughness

### DISK AND WIRE DICING SAW Model 15, Logitech, UK

00



Precision cutting of single crystals and wafers

Rapid change from disk to diamond wire saw Controlled saw pressure Automatic hydraulic sample feed Micrometer translator and limb for sample positioning Maximum cut depth:

50 mm

### AUTOMATIC DICING SAW DISCO DAD3220 DISCO DAD 3220, Japan



201

Blade dicing and grooving with extra-high precision

Single sp	indle	
Max. rev	olution speed:	40 000 rpm <sup>-1</sup>
X-axis		
	feed speed range:	0.1—500 mm/s
Y-axis		
	spindle offset step:	0.1 µm
	positioning accuracy:	5 µm
Z-axis		
	repeating accuracy:	1 µm
	kpiece diameter:	150 mm
Max. blad		58 mm
	thickness d:	10 µm
	ting depth (at d<100 µm):	dx20
	ic, semi-automatic or manual operation	
	f discs available to cut broad range of mater	ials
Capabilit	y of multistep cutting	

### HIGH TEMPERATURE FURNACE LHT 01/17 D/P480, Nabertherm, Germany

2019



Compact high-temperature furnace with molybdenum disilicide heaters

Maximum temperature:	1650 °C
Chamber volume:	1 dm <sup>3</sup>
Power:	2.2 kW
Thermocouple type:	S
Controller:	P480
Chamber dimensions (W x D x H):	110×120×120 mm <sup>3</sup>
Oven dimensions (W x D x H):	385×425×525 mm <sup>3</sup>
Heating time to max temperature:	10 min

### CHAMBER FURNACE LHT 08/18, Nabertherm, Germany



019

Compact high-temperature furnace with molybdenum disilicide heaters

### TUBE FURNACE R 50/250/13/C450, Nabertherm GmbH, Germany

202



Compact tube furnace with integrated adjustment devices

Maximum temperature:	1300°C
Maximum heating rate:	5°C/min
Annealing in an inert gas environment:	$N_2$ , Ar, $O_2$
Vacuum annealing	0.06 Torr

#### MUFFLE ELECTRIC FURNACE TK.8-1150.M.1F, Termokeramika LLC, Russia



201

Muffle furnace with annealing function according to a given temperature profile

Maximum operating temperature of the furnace: 1150 °C

Dimensions of the working chamber

of the furnace (WxDxH): 180×285×180 mm

Working environment: air

Number of temperature control zones: 1

Temperature control: automatic
Thermocouple type: K

Heating element: X23Ю5T (Alloy 875 analogue)

Chamber volume: 8 dm<sup>3</sup>

Furnace installed power: 13 kW

### RAPID THERMAL ANNEALING SYSTEM STE RTA100, SemiTEq, Russia

022



Installation for rapid annealing of samples and thermal activation of contact layers in a controlled inert environment

Optical pyrometer for surface temperature control Ability to program «multi-stage» annealing profile

Ultimate residual pressure in the chamber (reactor)	< 10 Torr
Maximum diameter of the processed plate	100 mm
Maximum heater power	18 kW
Maximum heating rate	30°C/sec
Maximum heating temperature	1000 °C
Annealing time	<b>1–600</b> s
Heating uniformity at 800°C	±2%

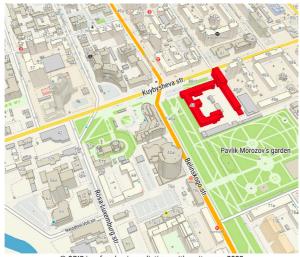


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